

TSM3911D 20V Dual P-Channel MOSFET



SOT-26

Pin Definition:

1. Gate 1 6. Drain 1 2. Source 2 5. Source 1



Key Parameter Performance

Parameter		Value	Unit	
V_{DS}		-20	V	
R _{DS(on)} (max)	$V_{GS} = -4.5V$	140		
	$V_{GS} = -2.5V$	200	mΩ	
	V _{GS} = -1.8V	300		
Q_g		15.23	nC	

Features

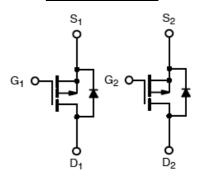
- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Ordering Information

Part No.	Package	Packing
TSM3911DCX6 RF	SOT-26	3kpcs / 7" Reel
TSM3911DCX6 RFG	SOT-26	3kpcs / 7" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-20	V	
Gate-Source Voltage		V _{GS}	±8	V	
Continuous Drain Current		I _D	-2.2	А	
Pulsed Drain Current		I _{DM}	-8	Α	
Continuous Source Current (Diode Con	iduction) (Note 1,2)	Is	-0.72	Α	
Maximum Power Dissipation	T _A = 25°C	P _D	1.15	14/	
	T _A =70°C		0.73	W	
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit	
Junction to Case Thermal Resistance	$R\Theta_{JF}$	30	°C/W	
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	80	°C/W	



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Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-0.45		-0.95	V
Gate Body Leakage	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
On-State Drain Current	$V_{DS} = -5V, V_{GS} = -5V$	I _{D(ON)}	-5			Α
Drain-Source On-State Resistance	$V_{GS} = -4.5V$, $I_{D} = -2.2A$			115	140	mΩ
	$V_{GS} = -2.5V, I_{D} = -1.8A$	R _{DS(ON)}		163	200	
	$V_{GS} = -1.8V, I_{D} = -1A$			220	300	
Forward Transconductance	$V_{DS} = -5V, I_{D} = -2.2A$	g _{fs}		5		S
Diode Forward Voltage	$I_S = -1.05A$, $V_{GS} = 0V$	V _{SD}		- 0.8	-1.2	V
Dynamic (Note 4)						
Total Gate Charge		Q_g		15.23		
Gate-Source Charge	$V_{DS} = -6V, I_{D} = -2.8A,$ $V_{GS} = -4.5V$	Q_gs		5.49		nC
Gate-Drain Charge		Q_{gd}		2.74		
Input Capacitance		C _{iss}		882.51		
Output Capacitance	$V_{DS} = -6V$, $V_{GS} = 0V$, f = 1.0MHz	C _{oss}		145.54		pF
Reverse Transfer Capacitance		C _{rss}		97.26		
Switching (Note 4,5)						
Turn-On Delay Time	$V_{DD} = -6V, R_L = 6\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$ $R_G = 6\Omega$	t _{d(on)}		17.28		
Turn-On Rise Time		t _r		3.73		
Turn-Off Delay Time		t _{d(off)}		36.05		ns
Turn-Off Fall Time		t _f		6.19		

Notes:

- 1. Pulse width limited by the Maximum junction temperature
- 2. Surface Mounted on FR4 Board, t ≤ 5 sec.
- 3. pulse test: PW ≤300µS, duty cycle ≤2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.

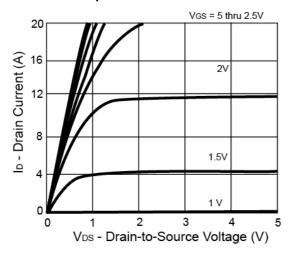


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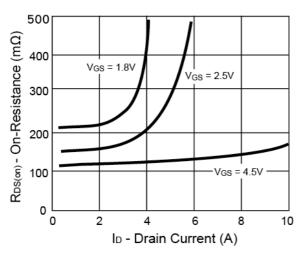


Electrical Characteristics Curves

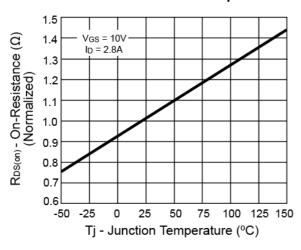
Output Characteristics



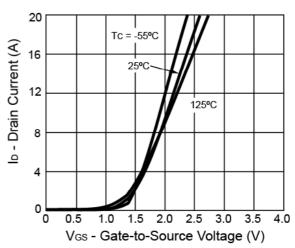
On-Resistance vs. Drain Current



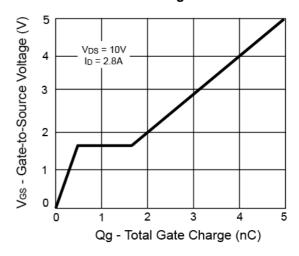
On-Resistance vs. Junction Temperature



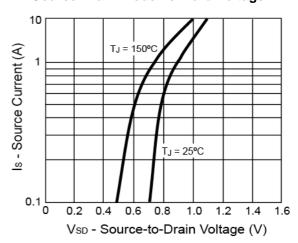
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



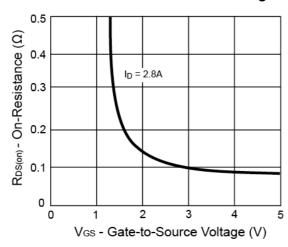


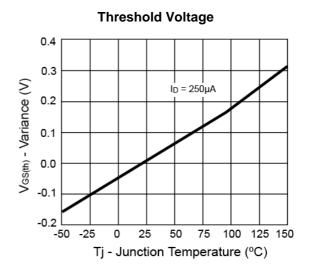
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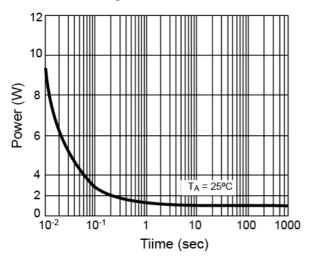
Electrical Characteristics Curves

On-Resistance vs. Gate-Source Voltage

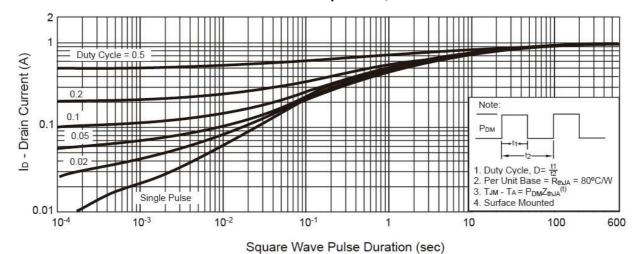




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

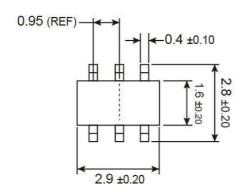


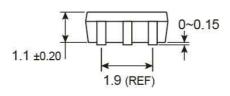


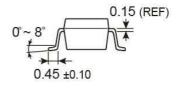
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SOT-26 Mechanical Drawing







Unit: Millimeters

Marking Diagram



1D = Device Code

Y = Year Code

M = Month Code

(**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apl, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)

= Month Code for Halogen Free Product

(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep,

X=Oct, Y=Nov, Z=Dec)

L = Lot Code



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